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America Semiconductor

"In America Semi We Trust"

MANUFACTURER OF WORLD CLASS HIGH POWER SEMICONDUCTORS

America Semiconductor

Silicon Bridge Rectifier

GBL06 thru GBL10

V_{RRM} = 50 V - 1000 V

I_F = 4 A

Features

- Plastic package has Underwriters Laboratory Flammability Classification 94V-0
- Types up to 1000 V V_{RRM}
- Ideal for printed circuit board
- High surge current capability
- High temperature soldering guaranteed: 250°C/ 10 seconds, 0.375(9.5mm) lead length
- Glass passivated chip junction
- High case dielectric strength

GBL Package

Mechanical Data

Case: Molded plastic body over passivated junctions
Weight: 0.071 oz, 2 g
Mounting position: Any
Terminals: Plated leads, solderable per MIL-STD-750 Method 2026 guaranteed

Maximum ratings, at T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions	GBL06	GBL08	GBL10	Unit
Repetitive peak reverse voltage	V_{RRM}		600	800	1000	V
RMS reverse voltage	V_{RMS}		420	560	700	V
DC blocking voltage	V_{DC}		600	800	1000	V
Continuous forward current	I_F	$T_C \leq 25$ °C	4	4	4	A
Surge non-repetitive forward current, Half Sine Wave	$I_{F,SM}$	T_C = 25 °C, t_p = 8.3 ms	150	150	150	A
Operating temperature	T_j		-55 to 150	-55 to 150	-55 to 150	°C
Storage temperature	T_{stg}		-55 to 150	-55 to 150	-55 to 150	°C

Electrical characteristics, at Tj = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions	GBL06	GBL08	GBL10	Unit
Diode forward voltage	V_F	I_F = 4 A, T_j = 25 °C	1.1	1.1	1.1	V
Reverse current	I_R	V_R = 50 V, T_j = 25 °C V_R = 50 V, T_j = 125 °C	5 500	5 500	5 500	µA
Thermal characteristics						
Thermal resistance, junction - case	R_{thJA} R_{thJL}		22.0 3.5	22.0 3.5	22.0 3.5	°C/W

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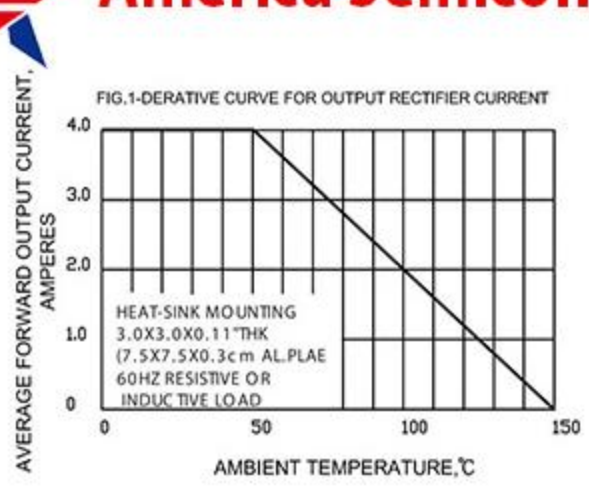
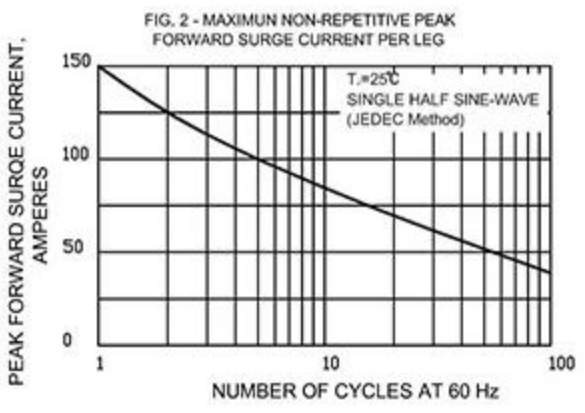
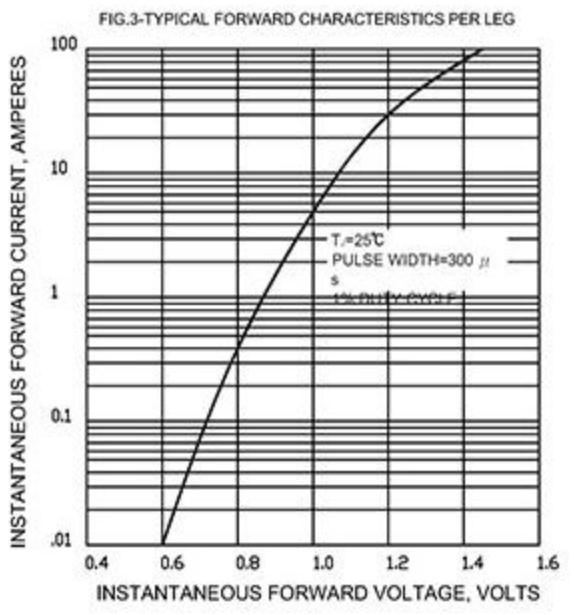
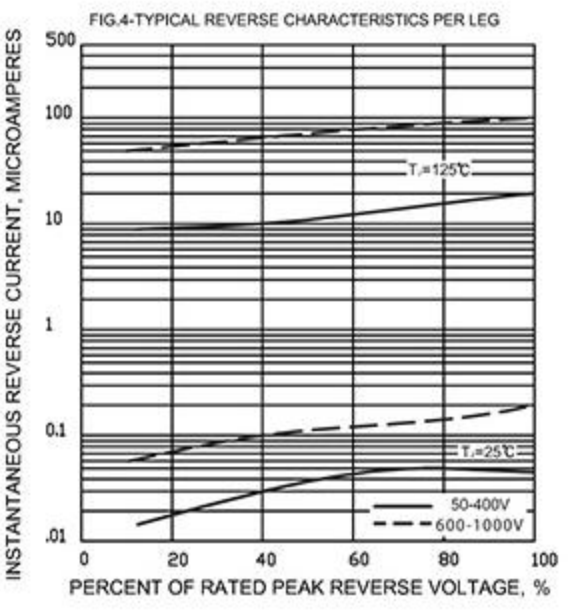
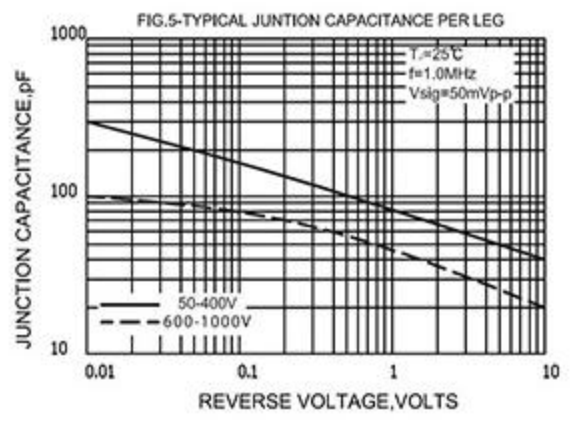
GBL06 thru GBL10

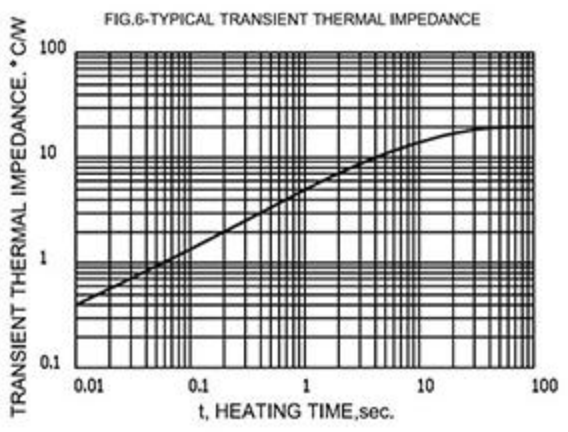












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